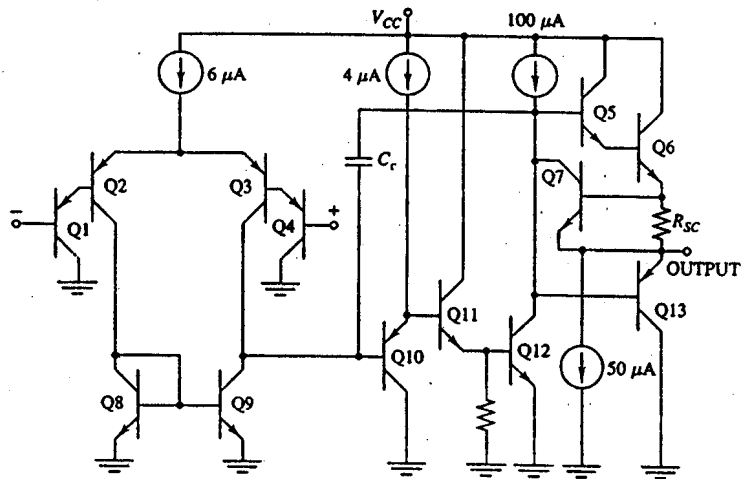




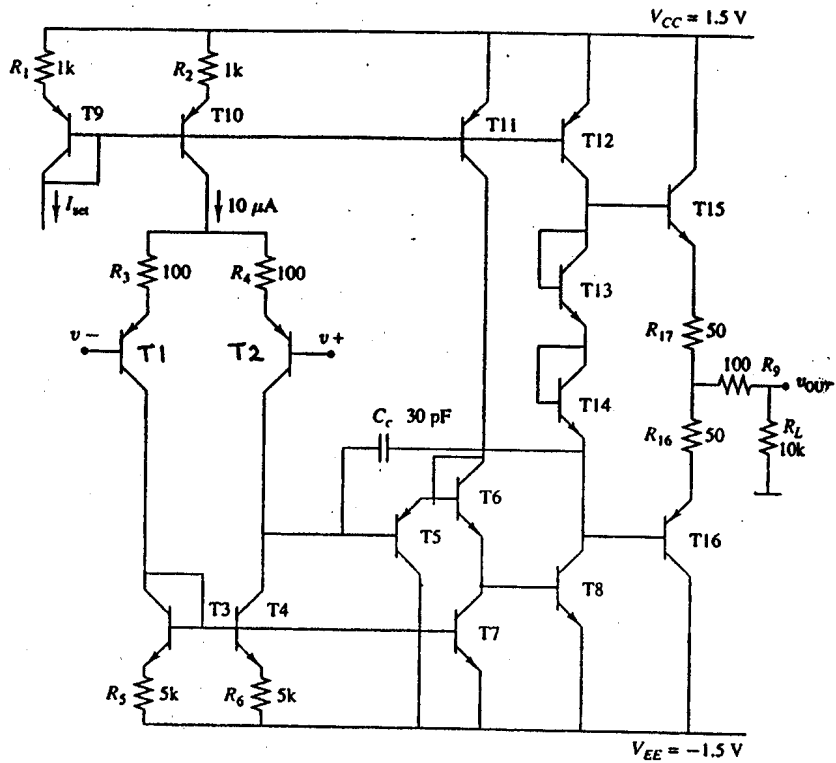
**BIPOLAR OP AMP LM-124 (NATIONAL SEMICONDUCTOR)**



Specifications		
Parameter	Value (at 3 V)	Unit
GBW	0.5	MHz
SR	0.4	V/μs
$r_{in}$	> 10	kΩ
$C_c$	15	pF
$A_{vo}$	≥ 110	dB
$I_e$	5	nA
$I_2 + I_3$	6	μA
$I_{10}$	4	μA
$I_{12}$	100	μA
$I_{tot}$	650	μA
$dv_{1eq,th}^2$	68	nV <sub>RMS</sub> /√Hz

Q7 - normally off  
(protection device)

BIPOLAR OP AMP LM-4250 (NATIONAL SEMICONDUCTOR)



Specifications (at  $I_{set} = 10 \mu A$ ):

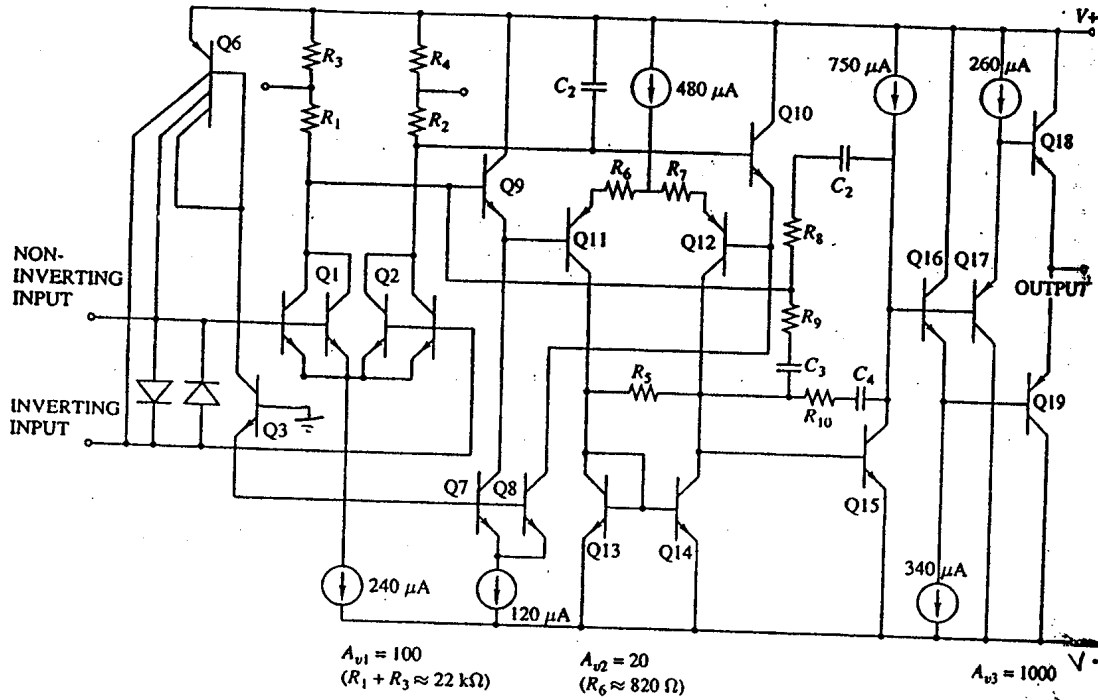
Parameter	Value (at $\pm 1.5 V$ )	Unit
GBW	0.25	MHz
SR	0.2	V/ $\mu s$
$R_L$	> 10	k $\Omega$
$C_c$	30	pF
$A_{v0}$	$\geq 110$	dB
$I_{\epsilon}$	50	nA
$I_{b,10}$	10	$\mu A$
$I_{11,12}$	14	$\mu A$
$I_{15}$	50	$\mu A$
$dV_{10,th}^2$	38	nV <sub>RMS</sub> / $\sqrt{Hz}$

T10, 11, 12 = current sources

Diff amp  $\rightarrow$  gain  $\rightarrow$  Class AB out stage

BIPOLAR OP AMP OP-27 (PRECISION MONOLITHICS INC)

FIGUR



Specifications		
Parameter	Value (at $\pm 15 \text{ V}$ )	Unit
GBW	8	MHz
SR	2.8	V/ $\mu\text{s}$
$R_L$	> 2	k $\Omega$
$C_c$	?	pF
$A_{v0}$	$\geq 125$	dB
$I_e$	12	nA
$I_1 + I_2$	240	$\mu\text{A}$
$I_{tot}$	3000	$\mu\text{A}$
$dv_{log,th}^2$	3	nV <sub>RMS</sub> / $\sqrt{\text{Hz}}$

Q1, Q2 diff pair  
 Q11, Q12 diff pair  
 Q15 CE

} 3 gain stages

Unusual Class AB out stage